

IN THE SPECIFICATION

5 Please amend the paragraph on page 3, lines 6 - 8, following
the SUMMARY OF THE INVENTION heading as follows:

10 The present invention provides a method of long-term low
temperature annealing of semiconductor devices to form ohmic
10 contact regions between a layer of wide band-gap semiconductor
material and ~~spaced-apart~~ contact areas disposed thereon.

15 Please amend the paragraph on page 5, line 19 through
page 6, line 9, as follows:

20 Contact layer 16, such as, for example, aluminum, zinc, nickel or other
similar metal, is formed by, for example, sputtering, chemical vapor
deposition, or other processes, over wide band-gap semiconductor material
layer 14. Contact layer 16 and wide band-gap semiconductor material layer
14 are in substantially continuous contact. As deposited and prior to
annealing, contact layer 16 forms a rectifying or otherwise non-ohmic
connection to wide band-gap semiconductor material layer 14. Contact layer
16 is typically patterned and etched by known methods to expose desired
25 portions of wide band-gap semiconductor material layer 14. Features (not
shown) are then etched in the wide band-gap semiconductor material layer 14
using known methods, and to form functional circuit structures and thereby a
functional semiconductor device 10. The portion or portions of contact layer
16 that remain after etching define one or more contact areas 20 (Fig. 2).

Please amend the paragraph on page 7, line 17 through
5 page 8 line 5, as follows:

Referring now to Fig. [[2]] 4, the current vs. voltage curves obtained between two spaced-apart contact regions 22 formed as a result of various annealing parameters are shown. In the exemplary embodiment of the
10 method of the present invention, a plurality of devices 10 were formed. Devices 10 included nickel (Ni) contacts 20 having an approximate thickness of from 2400 to 2600 Angstroms. The contacts 20 were deposited via electron beam evaporation at a background pressure of approximately 1×10^{-7} Torr onto a wide band-gap semiconductor material layer 14 of 4H silicon carbide (SiC). The devices 10 were then divided into several groups of one or
15 more devices. Each group was then subjected to respective annealing processes of correspondingly different temperatures and/or durations.

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Please amend the paragraph on page 11, lines 18 – 21, as follows:

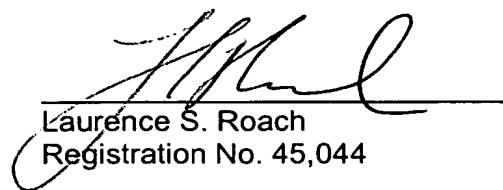
In the embodiment shown, the wide band-gap
25 semiconductor material is configured as 4H silicon carbide. However, it is to be understood that the method of the present invention is equally applicable to different poly-types of silicon carbide, such as, for example, ~~6H-SiC and 3C-SiC~~. 6H-SiC and 3C-SiC.

Respectfully submitted,

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Date



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